AMENDMENTS TO THE CLAIMS

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

1-20. (Cancelled)

21. (Currently Amended) A method for fabricating a liquid crystal display device comprising:

forming a first metal seed layer on a glass substrate;

depositing a first metal layer on the first metal seed layer using an electric plating method;

patterning the first metal seed layer and the first metal layer to form a gate line and a gate electrode;

forming a gate insulating film on an entire surface including the gate line;

forming a semiconductor layer on the gate electrode;

forming a second metal seed layer on the entire surface including the semiconductor layer;

depositing a second metal layer on the second metal seed layer using the electric plating method;

patterning the second metal seed layer and the second metal layer to form a data line crossing the gate line and source/drain electrodes on the semiconductor layer; and

forming a pixel electrode connected with the drain electrode, on a passivation film formed on the entire surface including the data line,

wherein the electric plating method includes the steps of:

arranging the substrate in a tub containing an electrolytic solution;

removing a metal oxide, wherein removing the metal oxide includes applying a first negative potential to the substrate;

providing a deposition solution to the tub having the electrolytic solution;

depositing a metal by applying a negative potential to the substrate, wherein depositing the metal includes applying a second negative potential to the substrate.

22. (Canceled)

23. (Currently Amended) The method of claim [[22]] 21, wherein the electric plating method is performed in such a manner that pH and potential of the electrolytic solution are controlled.

24. (Currently Amended) The method of claim [[22]] 21, wherein the step of removing the metal oxide film and the step of depositing the metal are performed within different chambers in the tub.

25. (Currently Amended) The method of claim [[22]] 21, wherein the electrolytic solution reduces the metal oxide film formed on the surfaces of the first and second metal seed layers to metal layers.

26. (Currently Amended) The method of claim [[22]] 21, wherein the electric plating method is performed at a temperature of about 25~100°C.

27. (Currently Amended) The method of claim [[22]] 21, wherein the electric plating method is performed within the range of current of about 10~100μA.

28. (Currently Amended) The method of claim [[22]] 21, wherein the deposition solution includes a metal which is the same as the metal of the first and second metal seed layer and does not react with the electrolytic solution.

29. (Original) The method of claim 21, further comprising the steps of forming another substrate to oppose the glass substrate and forming a liquid crystal between the two substrates.

30. (Original) The method of claim 21, wherein the first and second metal seed layers are formed of a metal material containing metal of the first and second metal layers.

31. (Original) The method of claim 21, wherein the first and second metal layers are formed of any one of Cu, Al, Cr, Mo, W, or an Al alloy.